

GR-65J075AK: DFN 8x8 Cascode GaN HEMT

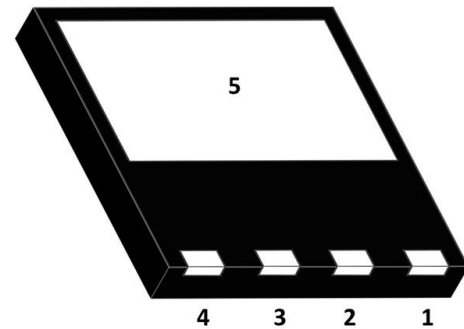
Description

GR-65J075AK is a normally-off GaN High electron mobility transistor (HEMT) device using the cascode configuration, which provides high breakdown voltage, high current and high operating speed which is suitable for high power applications.

Key Specifications

Part Number	GR-65J075AK
V_{DS}	650V
$V_{(TR)DS}$	800V
$R_{DS(ON)}$, typ.	74m Ω
Q_G , typ.	12.4nC
Package	DFN 8 x 8 mm

GR-65J075AK (8080-CM)



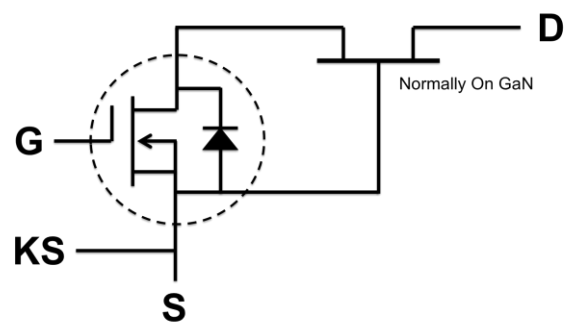
Gate: 1
Kelvin Source: 2
Source: 3, 4
Drain: 5

Features

- Gate drive voltage compatibility (-20V to +20V)
- High operating frequency
- Pin to Pin with CoolMOS/SJ and SiC MOSFET
- Low Q_{rr}
- ESD-resistant
- Comply with JEDEC standards

Applications

- Switch Mode Power Supplies (SMPS)
- AC-DC/DC-DC Converters: Boost, Buck, QR Flyback, ACF, AHB, LLC, Half/ Full Bridge Application
- Motor Drives, Lighting, Server



Cascode Device Structure

1- Electrical Characteristics

➤ **Table 1 Absolute maximum ratings**

Symbol	Parameter	Value	Unit
V_{DSS}	Drain-source voltage	650	V
$V_{(TR)DSS}$	Transient drain to source voltage ^a	800	V
V_{GSS}	Gate- source voltage	-20 ~ +20	V
I_D	Drain current (continuous) at $T_C = 25^\circ\text{C}$ operation	22.5	A
	Drain current (continuous) at $T_C = 100^\circ\text{C}$ operation	14.3	A
$I_{D,pulse}$	Pulsed drain current (pulse width: 10 μs)	84.4	A
P_D	Maximum power dissipation $T_C=25^\circ\text{C}$	78	W
T_C	Operating temperature	Case	-55 to +150 $^\circ\text{C}$
T_J		Junction	-55 to +150 $^\circ\text{C}$
T_S	Storage temperature	-55 to +150	$^\circ\text{C}$
T_{SOLD}	Soldering peak temperature ^b	260	$^\circ\text{C}$
MSL	Moisture sensitivity level	MSL3	

a. In off-state, spike duty cycle $D < 0.01$, spike duration $< 1\mu\text{s}$

b. For 10 sec., 1.6mm from the case

➤ **Table 2 Thermal Characteristics**

Symbol	Parameter	Value	Unit
$R_{\theta JA}$	Thermal resistance junction-ambient	63	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal resistance junction-case	1.6	$^\circ\text{C/W}$

➤ **Table 3 ESD Rating**

Symbol	Reference	Value	Unit
HBM (G-S) (G-D)	ANSI/ESDA/JEDEC JS-001-2024	2000	V
HBM (D-S)	ANSI/ESDA/JEDEC JS-001-2024	8000	V

➤ **Table 4** Electrical Characteristics ($T_{CASE} = 25\text{ }^{\circ}\text{C}$ unless otherwise stated)

Symbol	Parameter	Conditions	Values			Unit
			min.	typ.	max.	
$V_{(BL)DSS}$	Drain-source voltage	$V_{GS}=0V$	650	-	-	V
$V_{GS(th)}$	Gate threshold voltage	$V_{GS}=V_{DS}$, $I_D=1mA$	2.0	3.0	4.0	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS}=10V$, $I_D=5A$, $T_J=25\text{ }^{\circ}\text{C}$	-	74	91	$m\Omega$
		$V_{GS}=10V$, $I_D=5A$, $T_J=150\text{ }^{\circ}\text{C}$	-	137	-	
I_{DSS}	Drain-source leakage current	$V_{GS}=0V$, $V_{DS}=650V$, $T_J=25\text{ }^{\circ}\text{C}$	-	3.0	60	μA
		$V_{GS}=0V$, $V_{DS}=650V$, $T_J=150\text{ }^{\circ}\text{C}$	-	15	-	
I_{GSS}	Gate-to-source forward leakage current	$V_{GS}=20V$	-	-	100	nA
	Gate-to-source reverse leakage current	$V_{GS}=-20V$	-	-	-100	
C_{ISS}	Input capacitance	$V_{GS}=0V$, $V_{DS}=400V$, $f=1\text{ MHz}$	-	766	-	pF
C_{OSS}	Output capacitance		-	31.8	-	
C_{RSS}	Reverse transfer capacitance		-	2.42	-	
Q_G	Gate charge	$V_{GS}=0\sim 10V$, $V_{DS}=400V$, $I_{DS}=5A$	-	12.4	-	nC
Q_{GS}	Gate-source charge		-	3.35	-	
Q_{GD}	Gate-drain charge		-	2.10	-	
Q_{OSS}	Output charge	$V_{GS}=0V$, $V_{DS}=0\text{ to }400V$	-	49.7	-	
$t_{D(on)}$	Turn-on delay time	$V_{DS}=400V$, $V_{GS}=0\text{ to }10V$, $I_{DS}=2A$, $R_G=25\Omega$	-	10.4	-	ns
$t_{D(off)}$	Turn-off delay time		-	16.9	-	
Q_{RR}	Reverse recovery charge	$I_S=5A$, $V_{DS}=400V$	-	7.8	-	nC

2- Typical Characteristic Curves

Fig 1. On-Region Characteristics

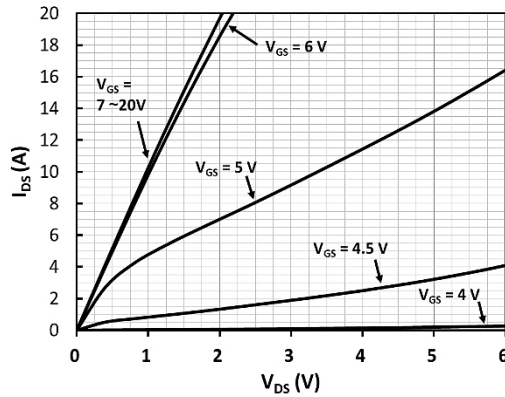


Fig 2. On-Resistance vs Drain Current and Temperature

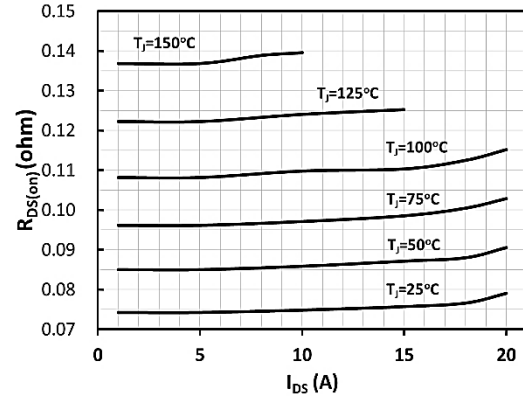


Fig 3. On-Resistance with Drain Current

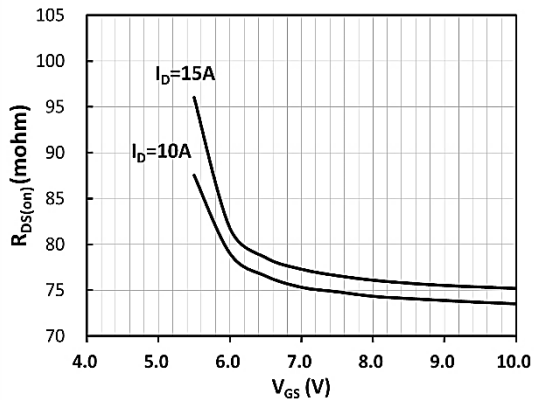


Fig 4. On-Resistance Variation with Temperature

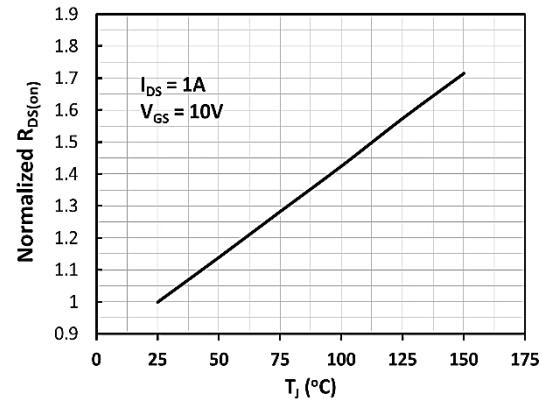


Fig 5. Threshold Voltage with Temperature

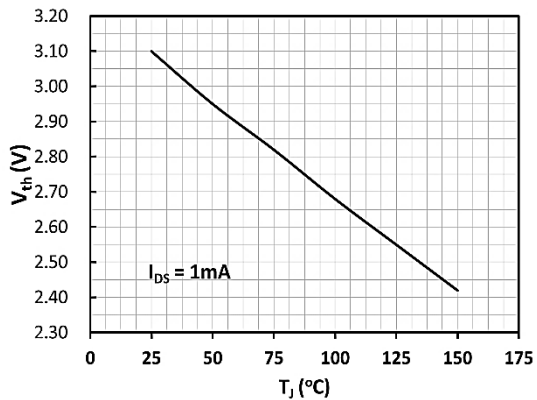


Fig 6. Capacitance Characteristics

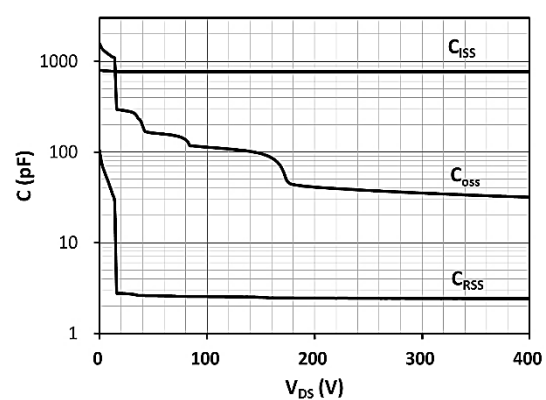


Fig 7. Gate Charge Characteristics, Qg

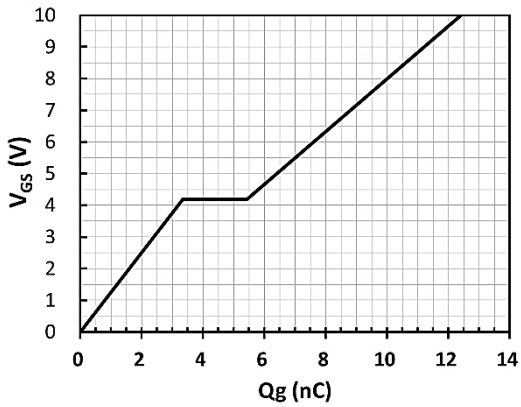


Fig 8. Capacitance Characteristics, Qoss

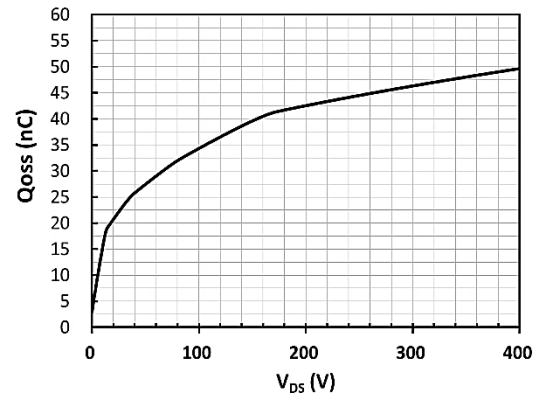
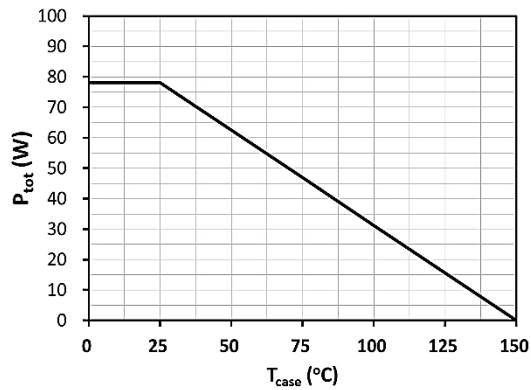
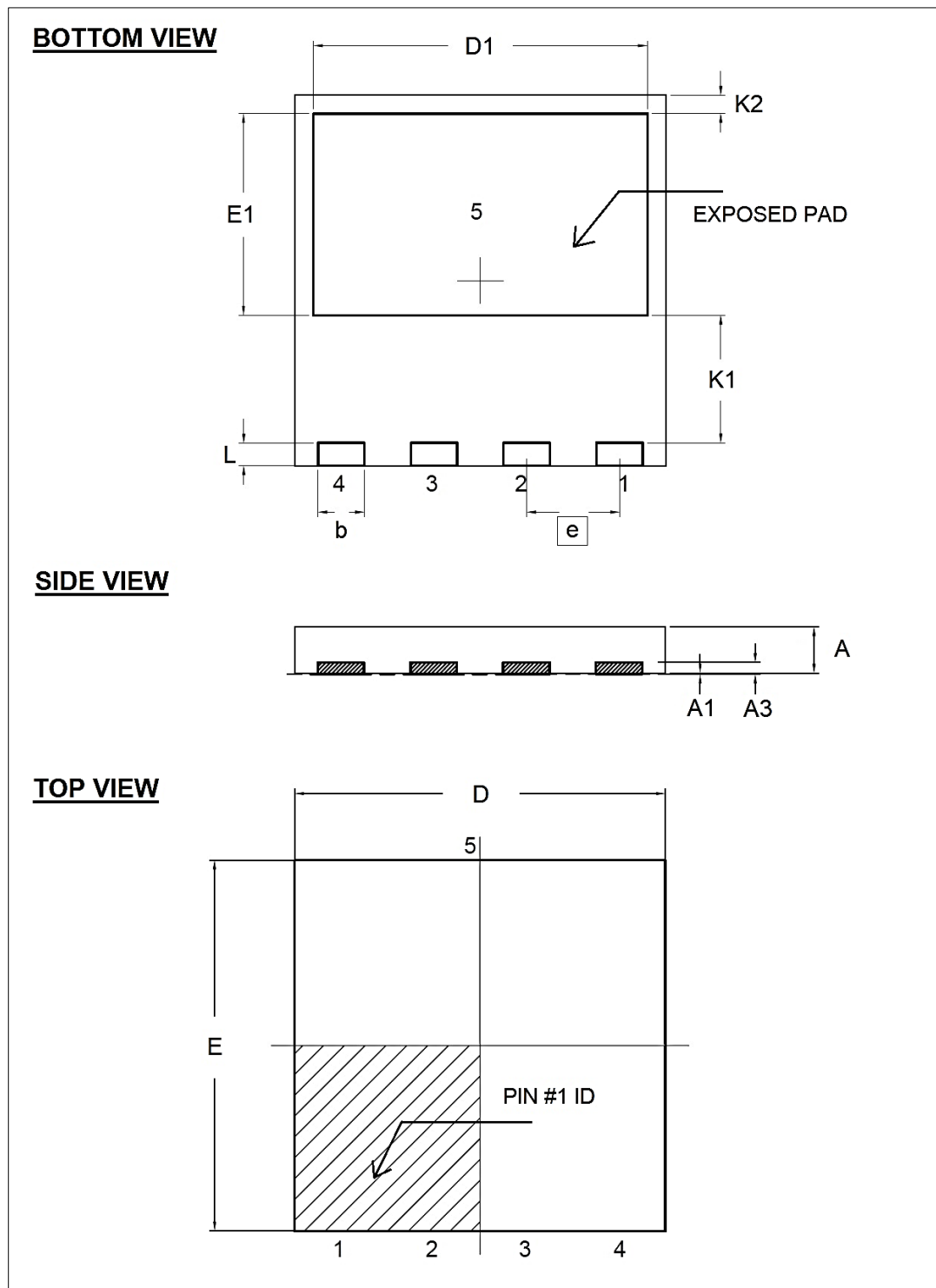


Fig 9. Power Dissipation Derating, Ptot



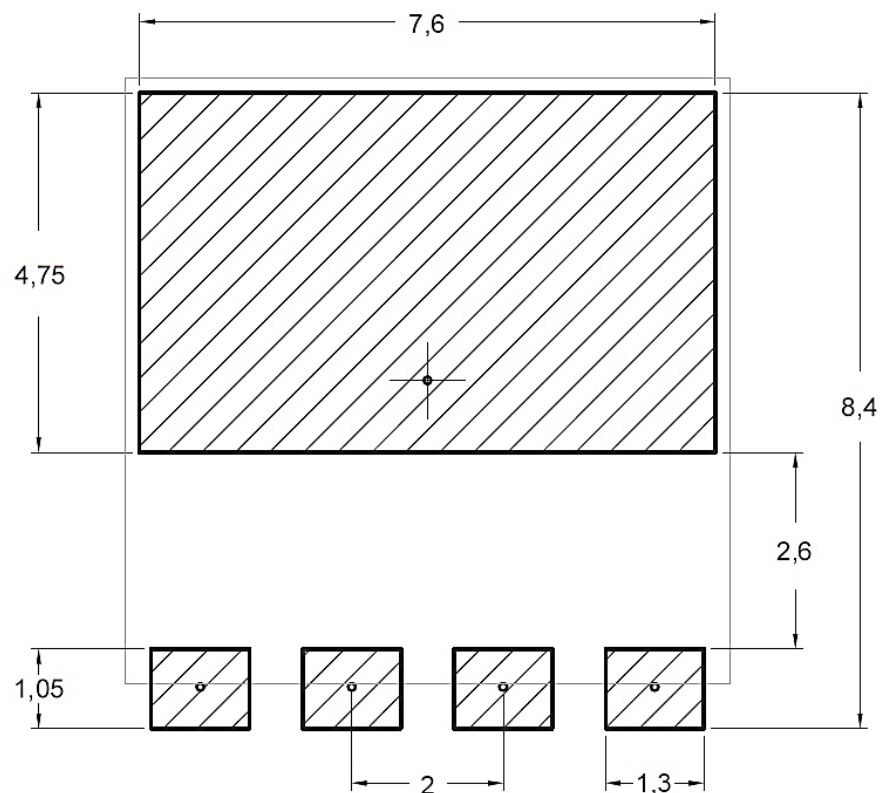
3- Package Outline Dimensions, GR-8080-CM



➤ Table 5 Dimension of GR-8080-CM

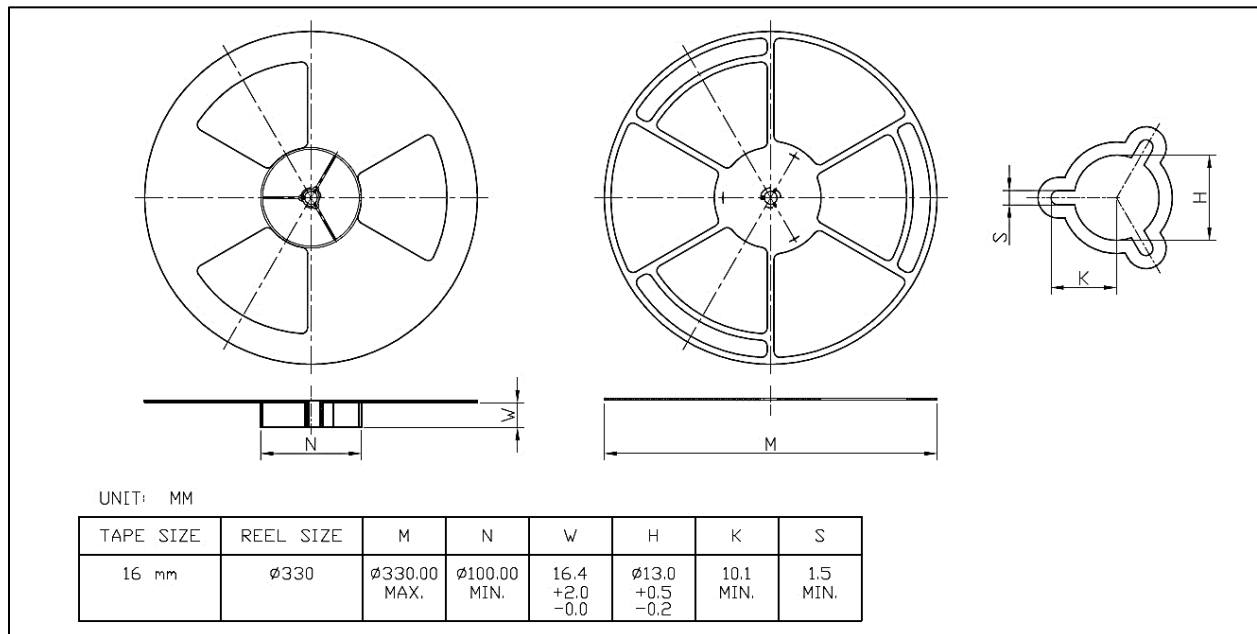
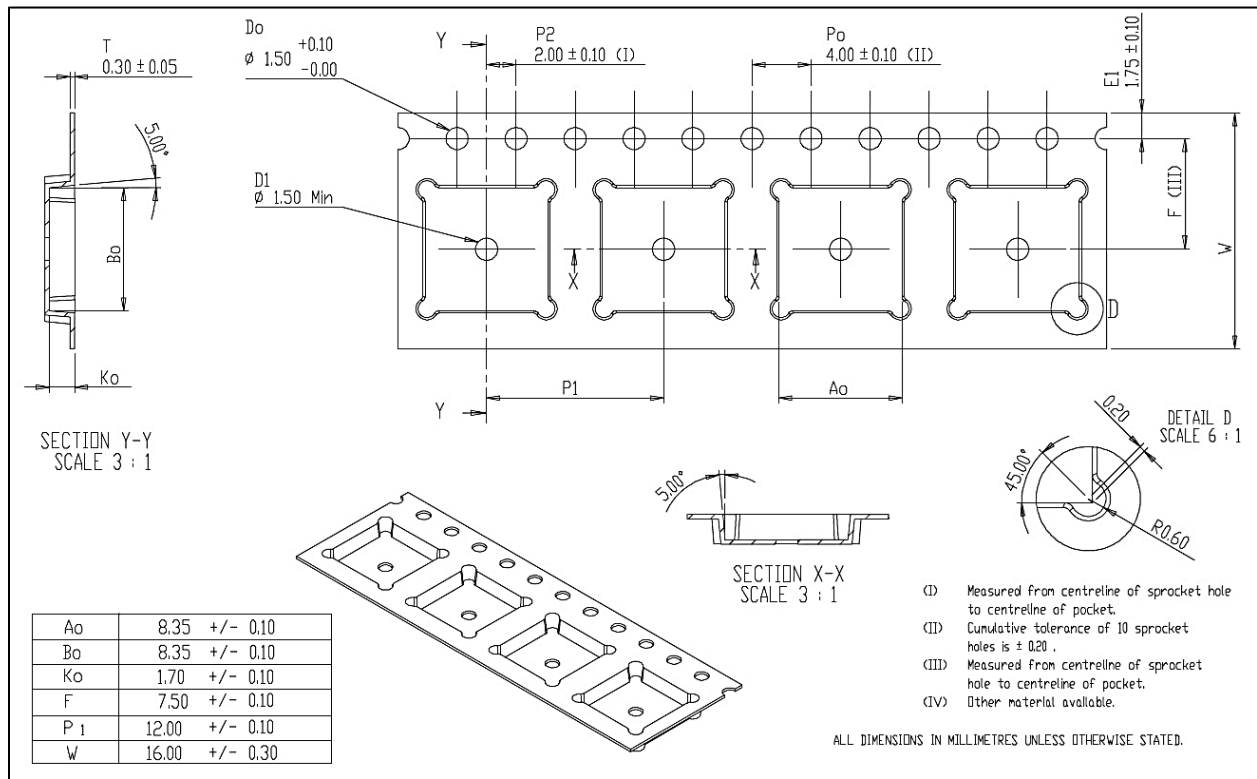
SYMBOL	DIMENSION (MM)			SYMBOL	DIMENSION (IN MM)		
	MIN.	NOM.	MAX.		MIN.	NOM.	MAX.
A	1.20	1.25	1.30	E	7.90	8.00	8.10
A1	--	0.02	0.05	E1	4.25	4.35	4.45
A3	0.203 REF.			L	0.40	0.50	0.60
b	0.90	1.00	1.10	K1	2.65	2.75	2.85
D	7.90	8.00	8.10	K2	0.30	0.40	0.50
D1	7.10	7.20	7.30	e	2.00 BSC		

GaNrich DFN-8080-CM Recommended PCB Soldering Footprint

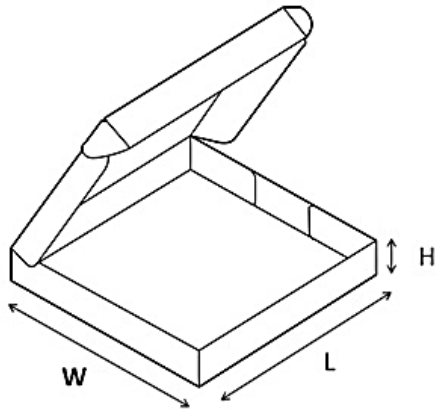


*According to IPC (IPC-A-610), solder voids are considered to be a defect when the overall calculated area of all voids in any given solder ball/joint is greater than 25% of the total solder ball area.

4- Tape and Reel Information

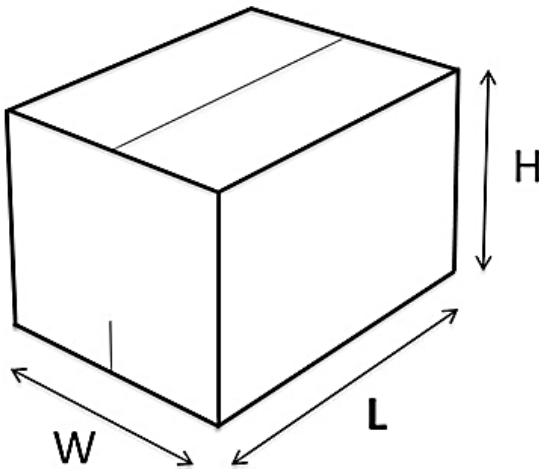


5- Box Dimensions



	Inner BOX, mm
W	340
L	360
H	50

1 Inner box contains 2500 components



	Outer Carton, mm
W	360
L	380
H	290

Each Carton contains 5 boxes,
Total of 12500 components

6- Change Log

Version	Date	Description
01	July 24, 2024	Initial version
02	Jan 3, 2026	Carrier tape information update
03	April 16, 2026	Electrical characteristics revised

- **Note:** GaNrich semiconductor reserves the right to revise products and/or specifications without notice.